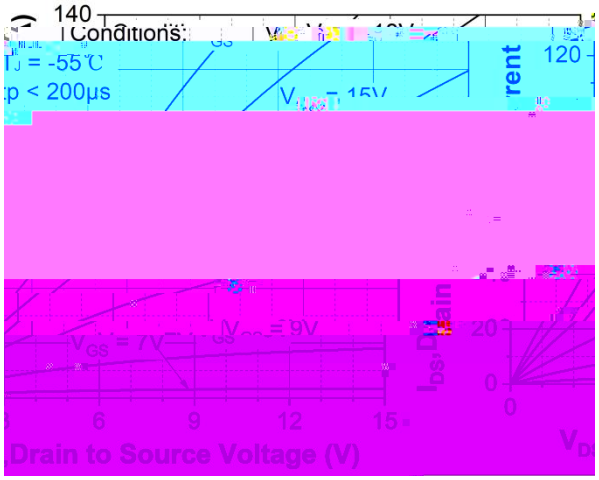
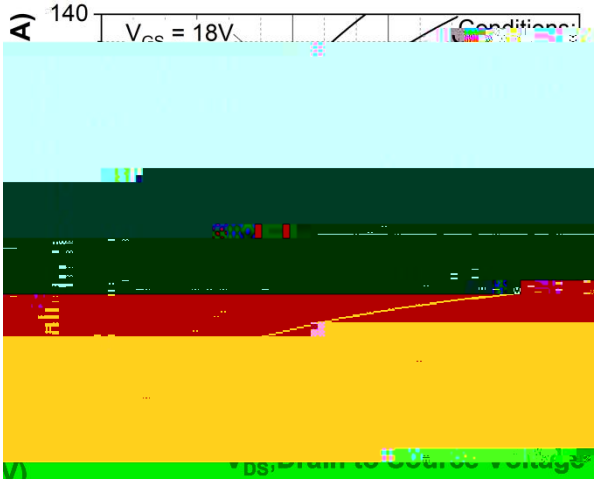
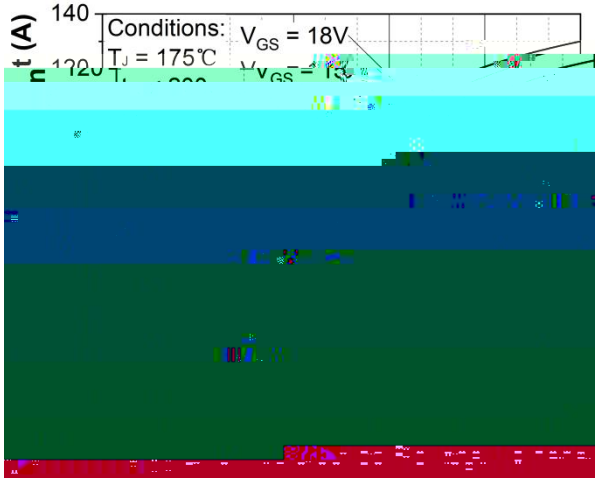
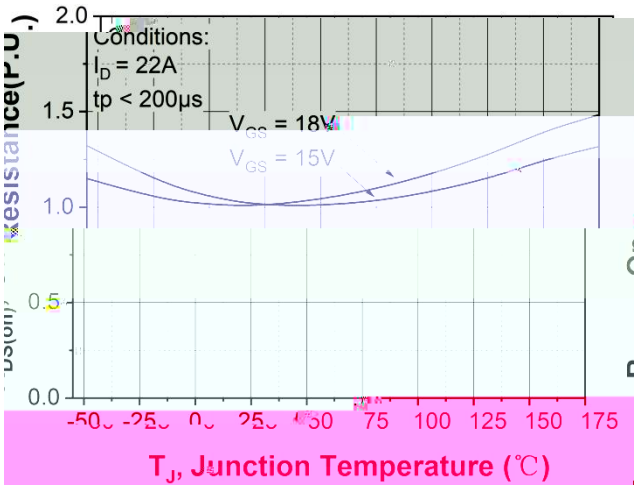
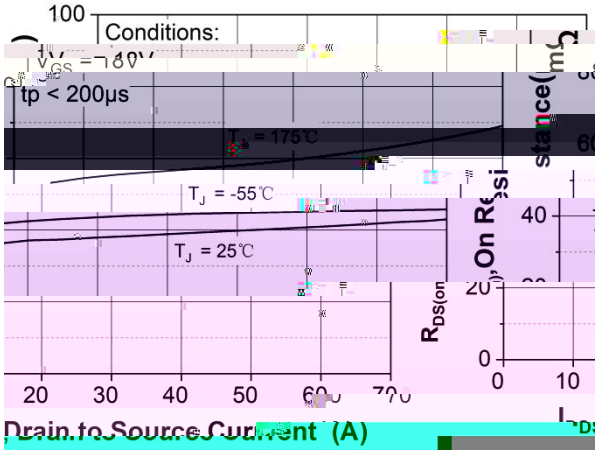


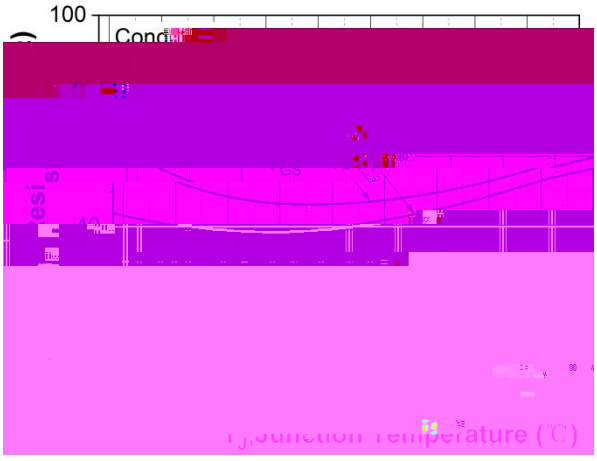

Conditions:
T_J = -55℃
tp < 200μs
V_{GS} = 7V
V_{GS} = 9V
Drain to Source Voltage (V)

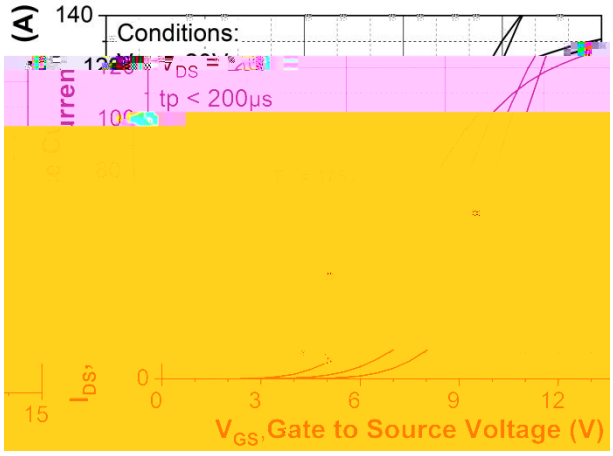

V_{GS} = 18V

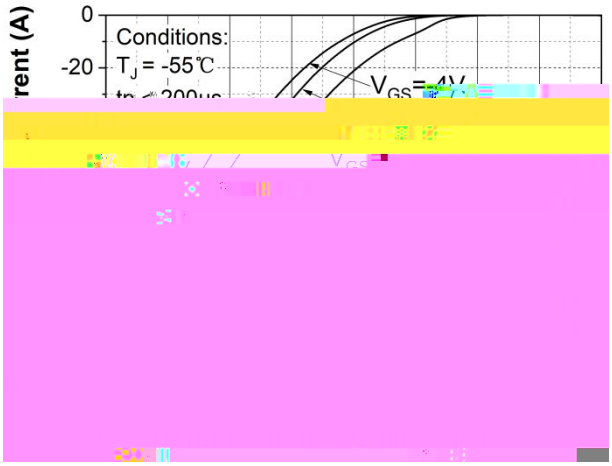

Conditions:
T_J = 175℃
V_{GS} = 18V

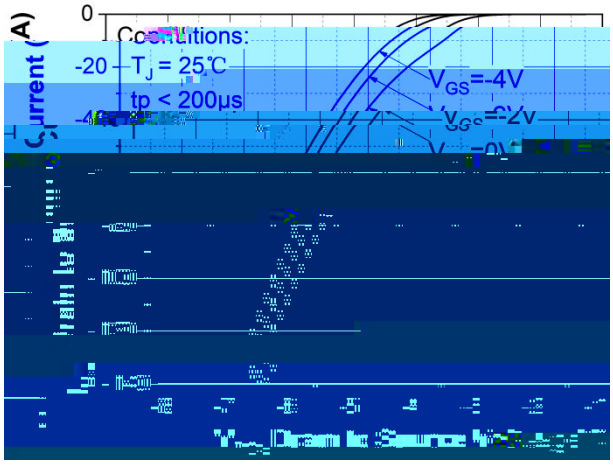

Conditions:
I_D = 22A
tp < 200μs
V_{GS} = 18V
V_{GS} = 15V
T_J, Junction Temperature (℃)

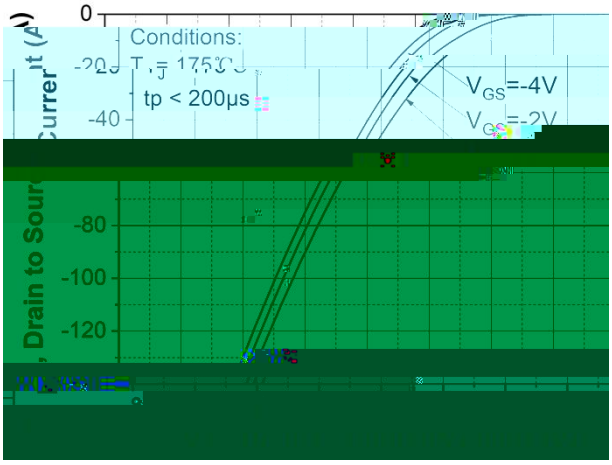

Conditions:
tp < 200μs
T_J = 175℃
T_J = -55℃
T_J = 25℃
Drain to Source Current (A)

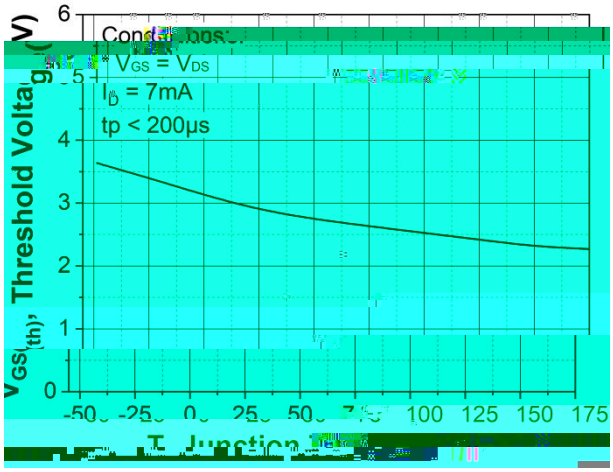


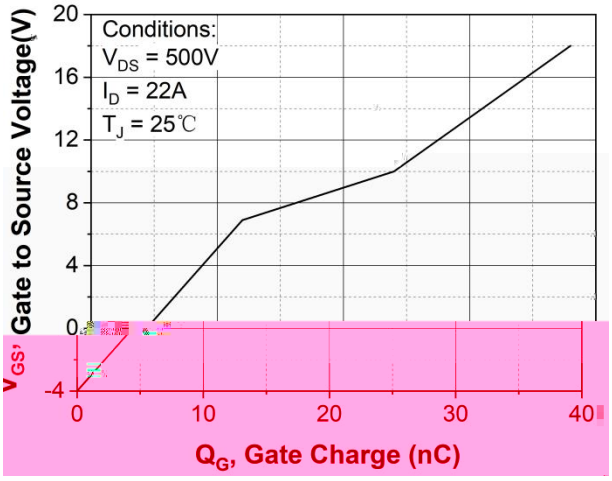

Conditions:
tp < 200μs
V_{GS}, Gate to Source Voltage (V)


Conditions:
T_J = -55℃
V_{GS}=-4V

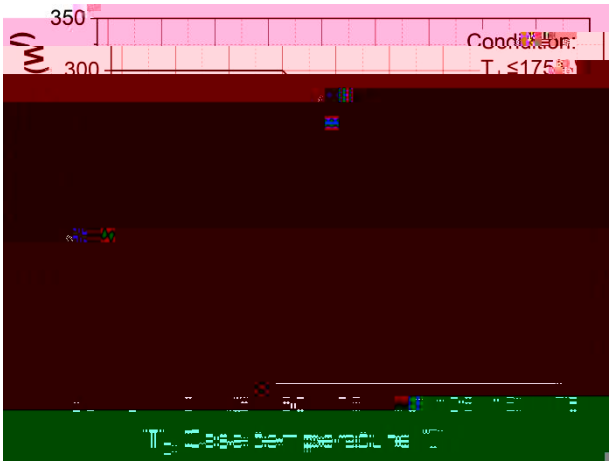

Conditions:
T_J = 25℃
tp < 200μs
V_{GS}=-4V

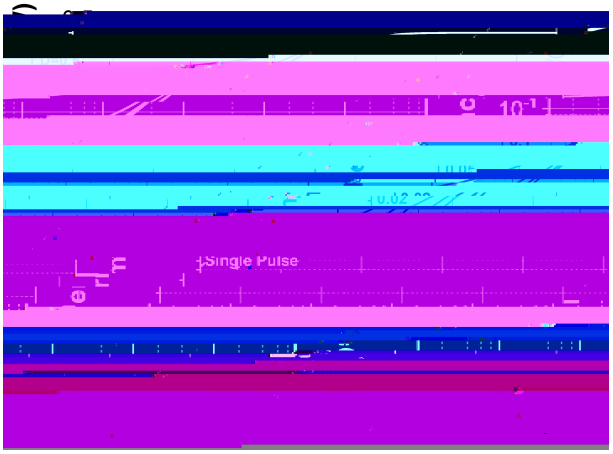

Conditions:
tp < 200μs
V_{GS}=-4V
V_{GS}=-2V

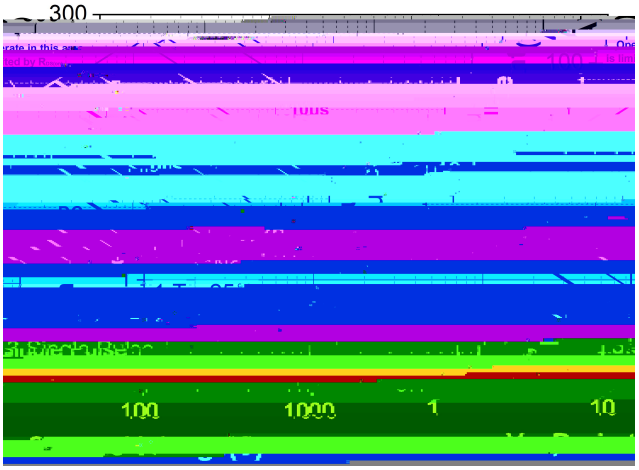

V_{GS} = V_{DS}
I_D = 7mA
tp < 200μs

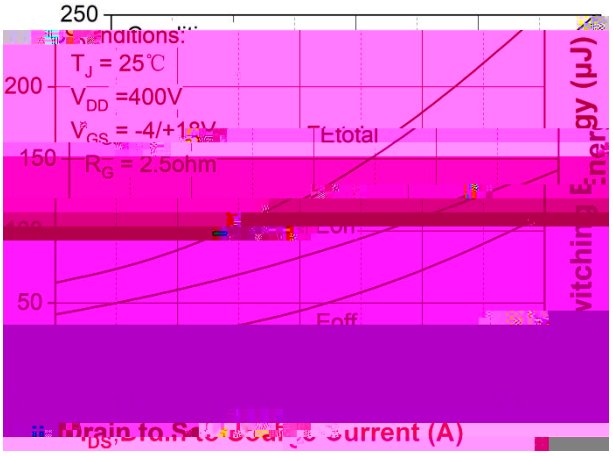

Conditions:
V_{DS} = 500V
I_D = 22A
T_J = 25℃
Q_G, Gate Charge (nC)

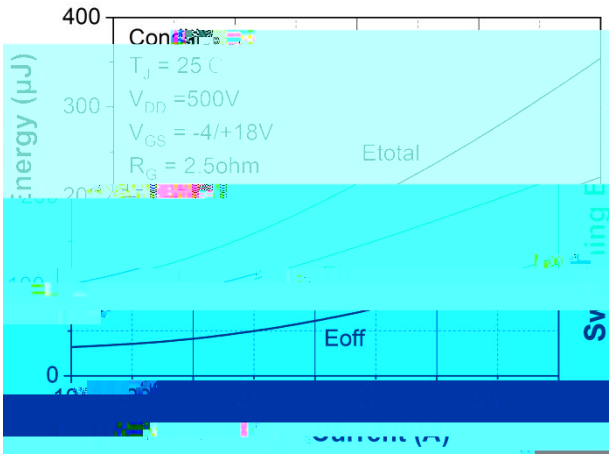


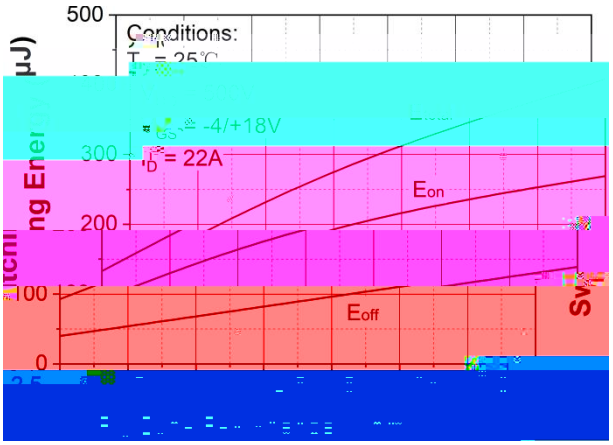

350
300
Condition:
T_J ≤175

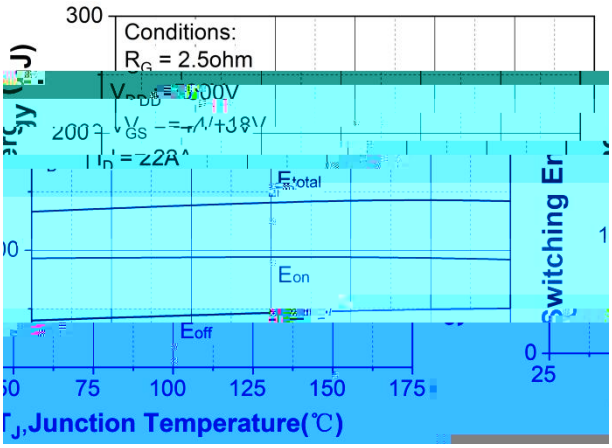

Single Pulse

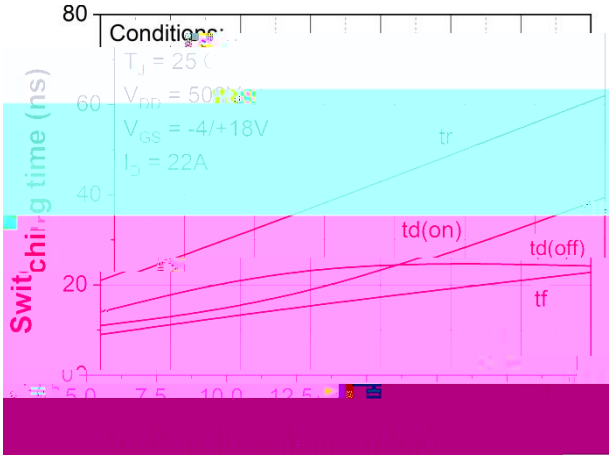

300
100
1,000
1
10

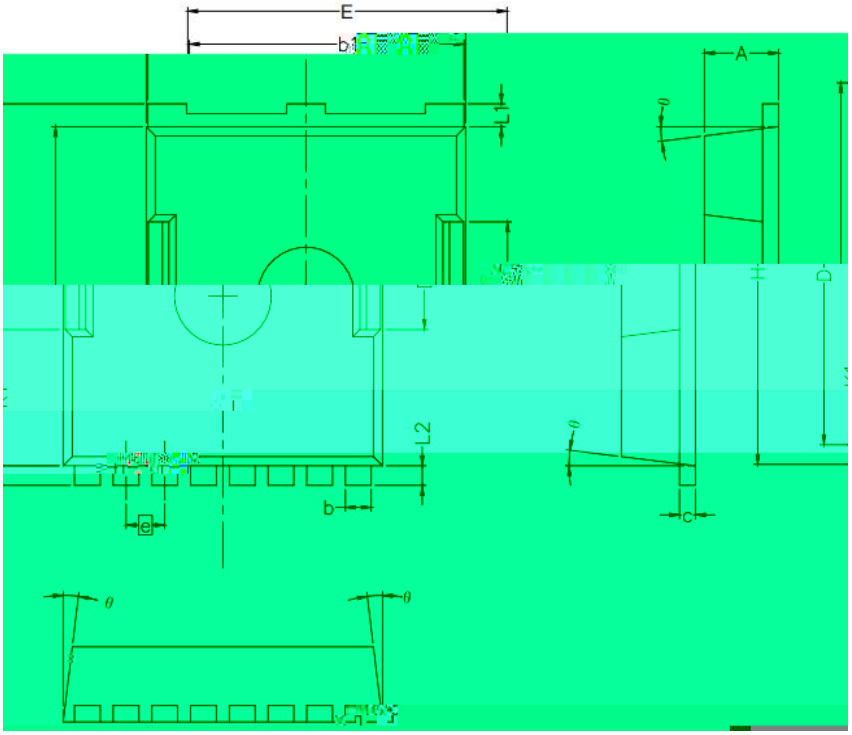

250
200
150
50
T_J = 25℃
V_DD =400V
V_GS = -4/+18V
R_G = 2.5ohm
Etotal
Eoff
Drain to Source Current (A)

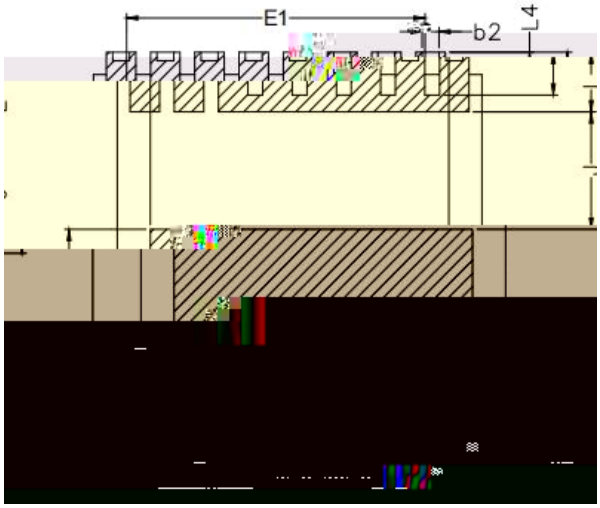

400
300
0
T_J = 25℃
V_DD =500V
V_GS = -4/+18V
R_G = 2.5ohm
Etotal
Eoff


500
Conditions:
300
200
100
0
Eon
Eoff

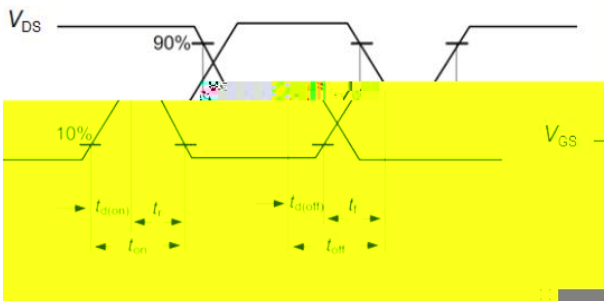

300
Conditions:
200
Etotal
Eon
Eoff
Switching Er
0
25
50
75
100
125
150
175
TJ,Junction Temperature(℃)

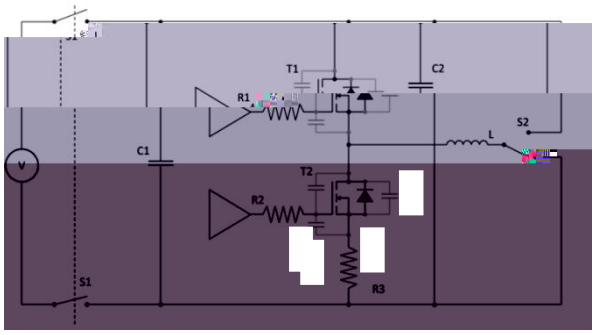

80
60
40
20
tr
td(on)
td(off)
tf

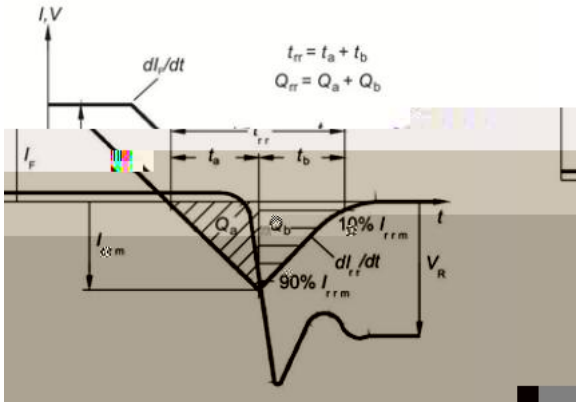




SYMBOL	DIMENSIONS MILLIMETERS	
	MIN	MAX
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20 BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4		


V_{DS}
90%
10%
V_{GS}
$t_{d(on)}$
t_r
t_{on}
$t_{d(off)}$
t_f
t_{off}


T1
C2
R1
S2
L
C1
V
T2
R2
R3
S1


I,V
dI_F/dt
$t_{rr} = t_a + t_b$
$Q_{rr} = Q_a + Q_b$
I_F
t_a
t_b
Q_a
Q_b
10% I_{rrm}
t
I_{rrm}
dI_{rr}/dt
90% I_{rrm}
V_R

		——	——
		——	——
		——	——
		——	——
			——